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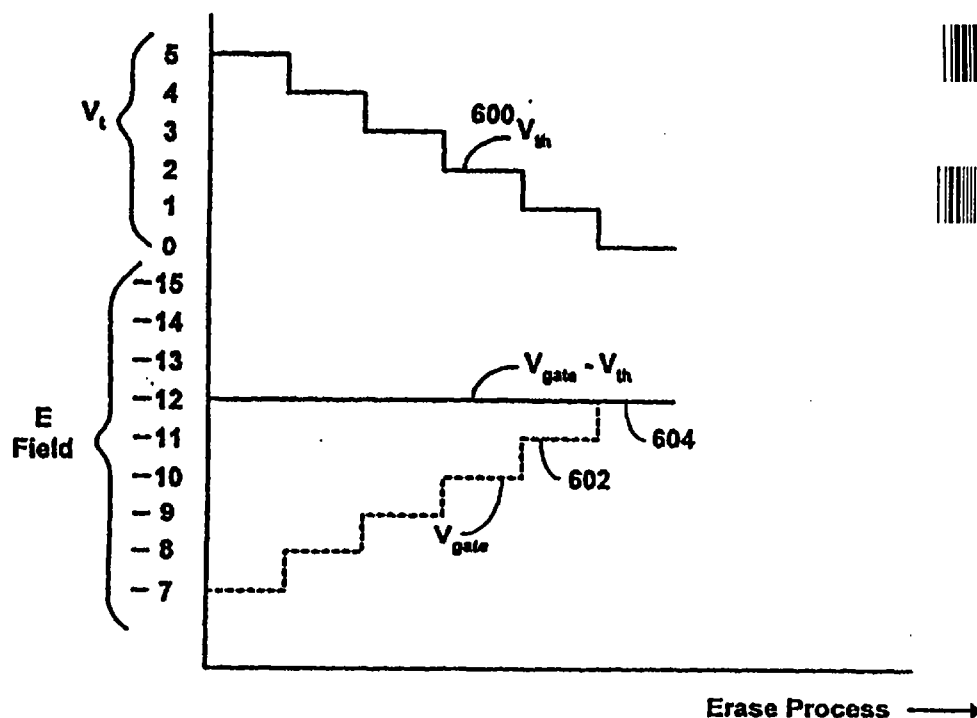
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(54) Title: METHOD TO PROVIDE A REDUCED CONSTANT E-FIELD DURING ERASE OF EEPROMS FOR RELIABILITY IMPROVEMENT



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(57) Abstract: A method to reduce the peak electric field during erase of a memory device composed of multiple memory cells. The electric field E_{field} of the memory cell during erase is determined by the equation $E_{\text{field}} = a_s(V_{\text{gate}} - V_{\text{th}}) + V_{\text{uv}} + (a_s - 1)V_{\text{source}}$ and varying gate voltages V_{gate} are applied to the gate of the cell being erased so that the $V_{\text{gate}} - V_{\text{th}}$ is constant during the erase procedure.